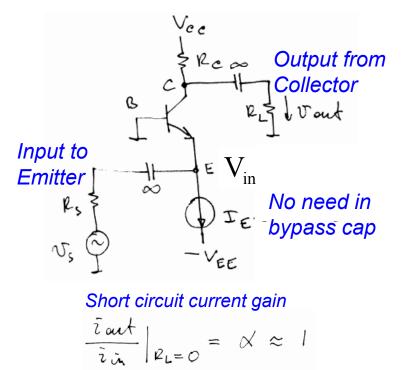
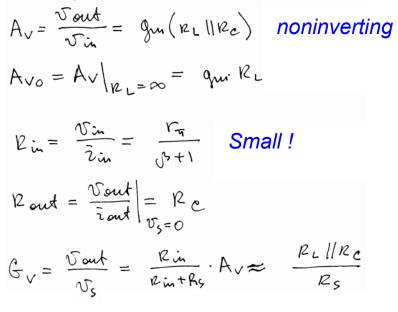
### ESE 372 / Spring 2011 / Lecture 19

# Common Base Biased by current source

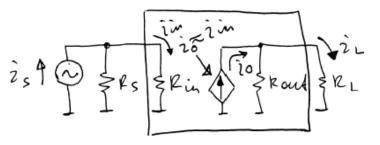


Start with bias DC analysis – make sure BJT is in FA, then calculate small signal parameters for AC analysis.

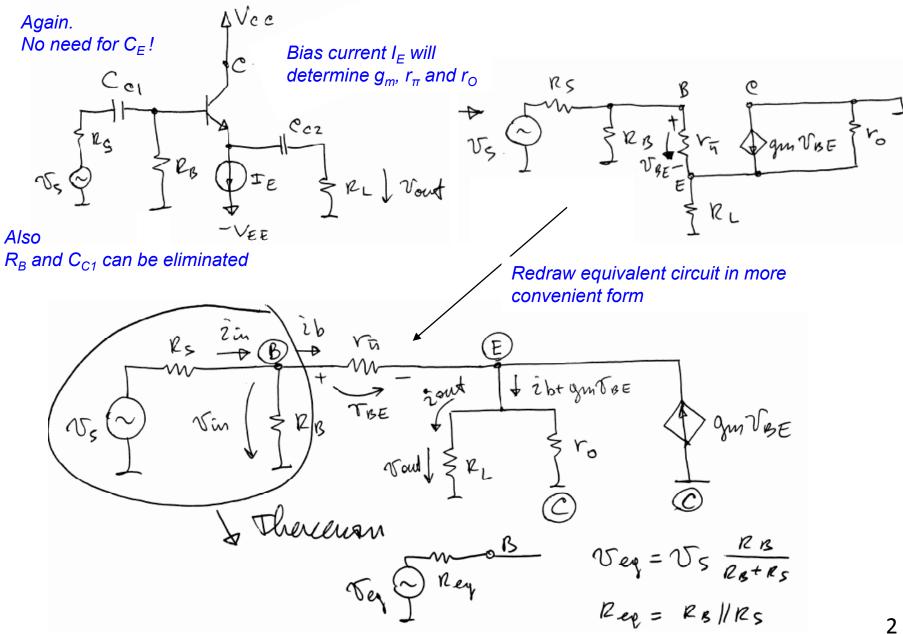
\*ignore r<sub>o</sub> for simplicity, then:

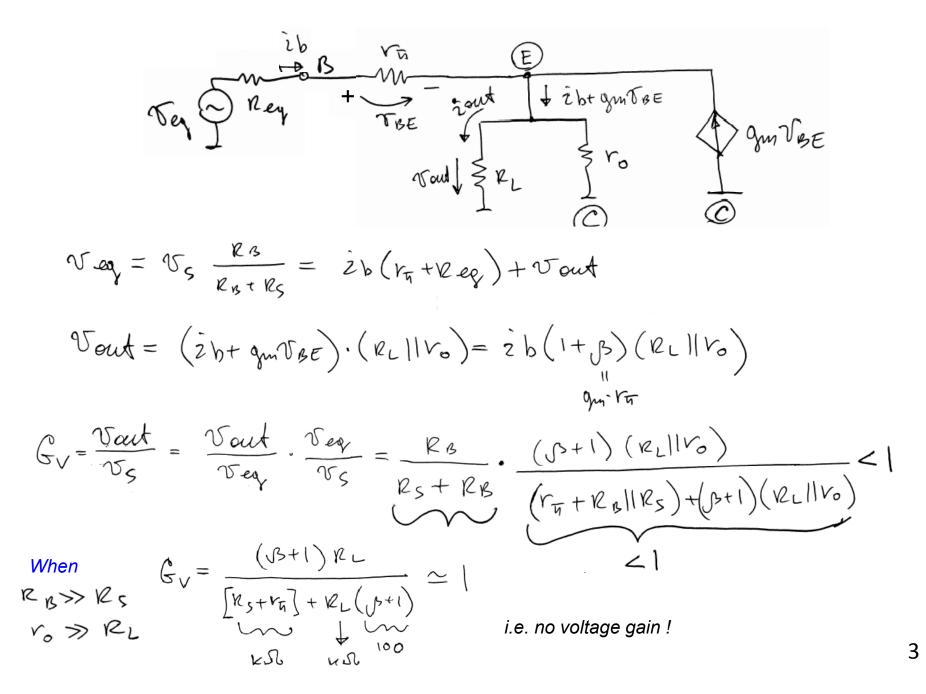


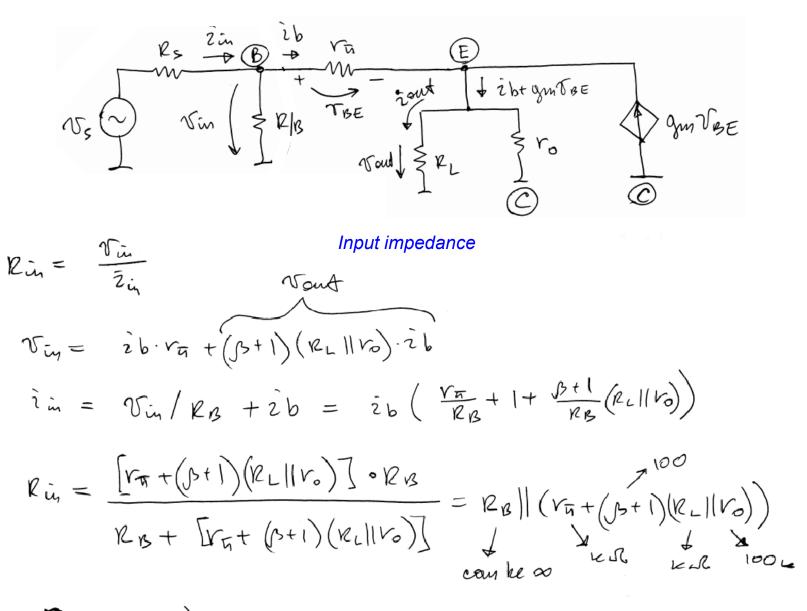
The circuit is current buffer: delivers current from source to load



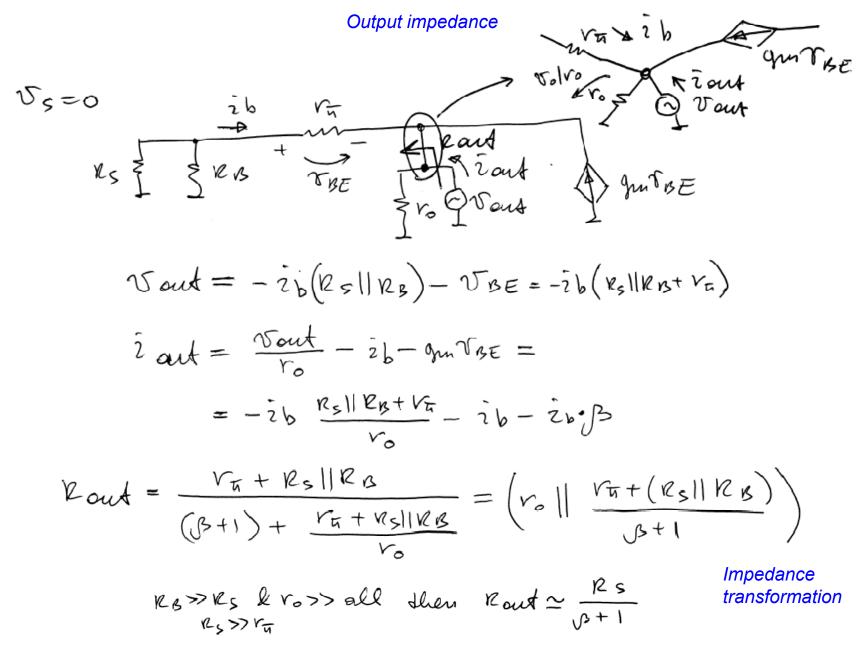
\* when BJT output impedance  $r_0$  can not be neglected – the circuit is said to perform an impedance transformation.



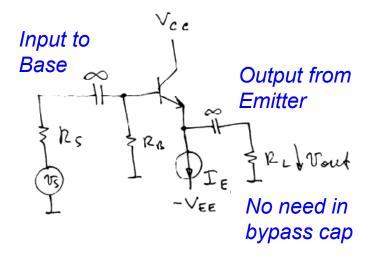




 $\mathcal{R}_{in} \approx (\mathcal{P} + 1) \cdot \mathcal{R}_{L}$ , for  $\mathcal{R}_{L} < \mathcal{V}_{o}$  Impedance transformation



## Common Collector (Emitter follower) Biased by current source



Short circuit current gain is almost the same as in case of CE amp, namely  $\beta$ +1.

Start with bias DC analysis – make sure BJT is in FA, then calculate small signal parameters for AC analysis.

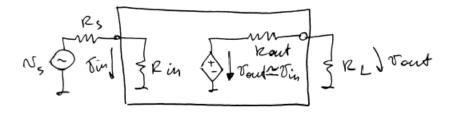
$$G_{v} = \frac{V_{out}}{V_{\varsigma}} = \frac{R_{B}}{R_{\varsigma} + R_{B}} \cdot \frac{(J+1)(R_{L} | V_{o})}{\left[(R_{\varsigma} | | R_{B}) + V_{\pi}\right] + (J+1)(R_{L} + V_{o})} < 1$$

Often 
$$R_B >> R_S$$
 and  $r_O >> R_L$ , then  
 $G_V \approx \frac{(J_{S+1}) \cdot R_L}{(R_S + V_{\overline{H}}) + R_L (J_{S+1})} \approx 1$ 

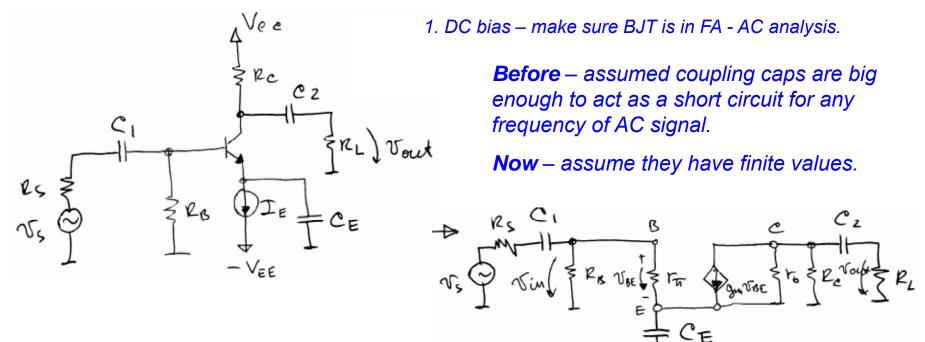
$$R_{in} = \frac{V_{in}}{\tilde{z}_{in}} = \left[ R_{\mathcal{B}} \| (v_{\overline{u}} + (\beta + 1)(R_{L}||v_{o}) \right] \approx (\beta + 1) \cdot R_{L}$$

$$\approx \sqrt{\kappa_{i} \mathcal{C}} \sim \kappa_{i} \mathcal{C} \sim \kappa_{i} \mathcal{C} \sim \kappa_{i} \mathcal{C} \sim \kappa_{i} \mathcal{C} \qquad \text{Impedances} \\ \text{transformed} \\ R_{out} = \frac{V_{out}}{\tilde{z}_{out}} \left| v_{\overline{s}=0} = v_{o} \right| \left| \frac{V_{\overline{u}} + (R_{s}||R_{\beta})}{\beta + 1} \approx \frac{R_{s}}{\beta + 1} \right]$$

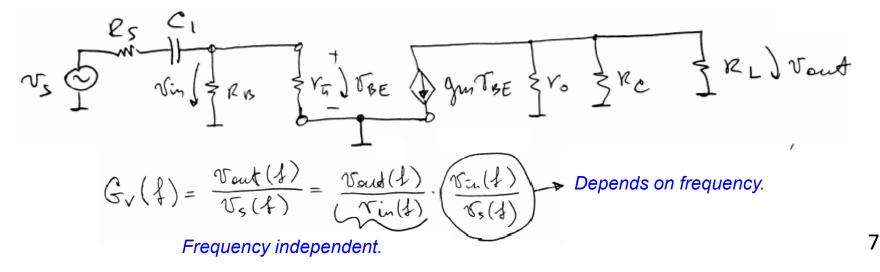
The circuit is voltage buffer: delivers voltage from source to load

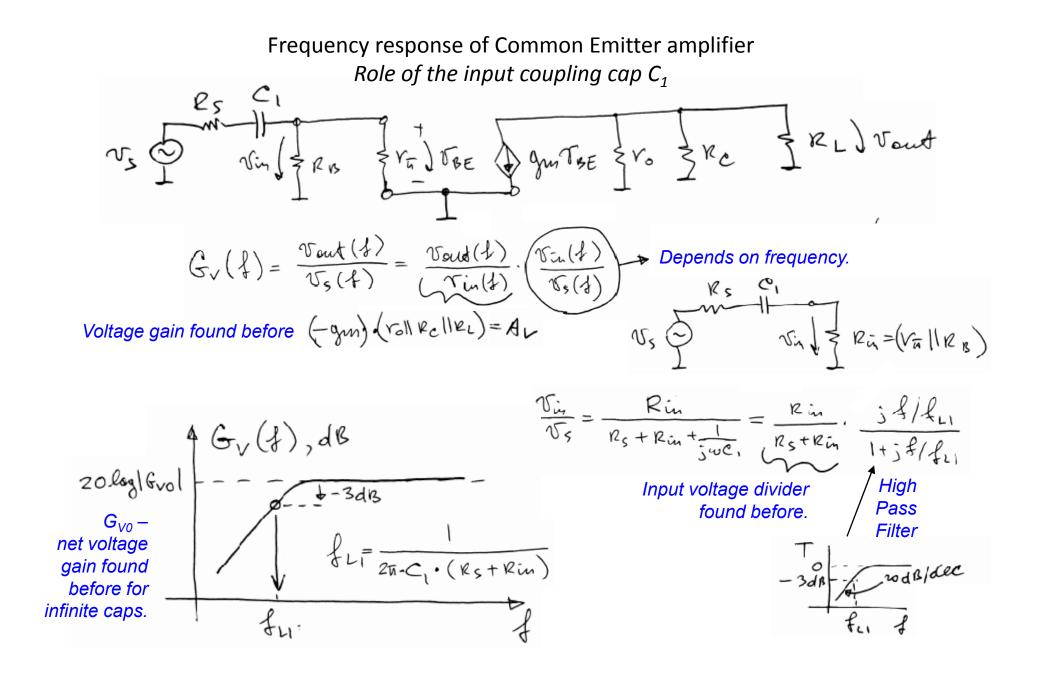


# Frequency response of Common Emitter amplifier Low frequencies, i.e. BJT itself is fast enough



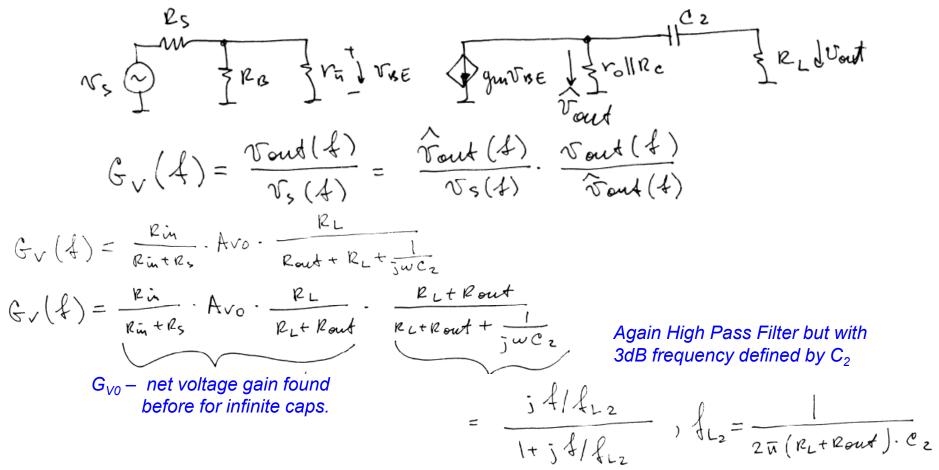
**1.** Assume  $C_1$  is finite while  $C_2$  and  $C_E$  are still infinite.





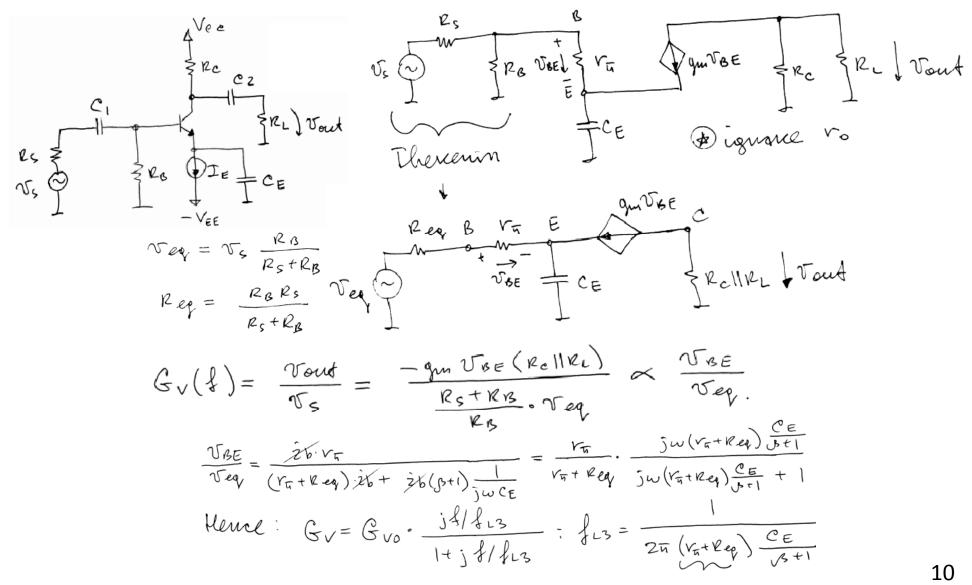
#### Frequency response of Common Emitter amplifier Role of the output coupling cap C<sub>2</sub>

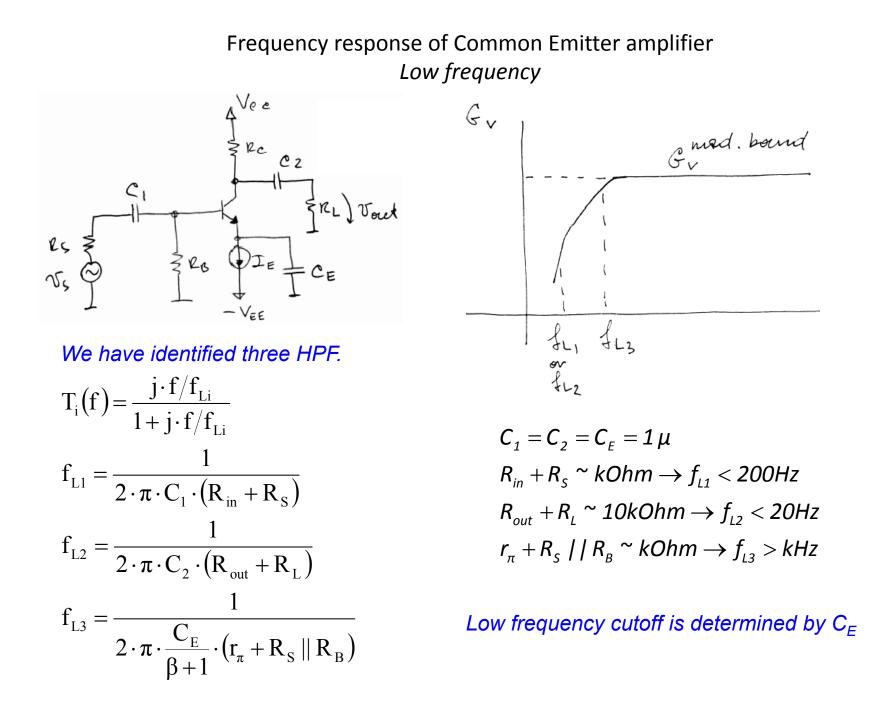
**2.** Assume  $C_2$  is finite while  $C_1$  and  $C_E$  are still infinite.



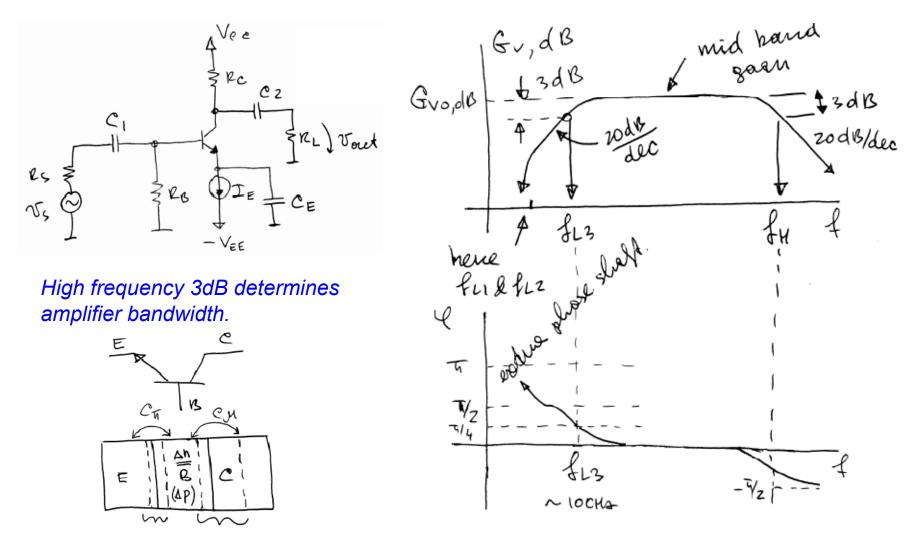
#### Frequency response of Common Emitter amplifier Role of the bypass cap $C_E$

**3.** Assume  $C_E$  is finite while  $C_1$  and  $C_2$  are still infinite.

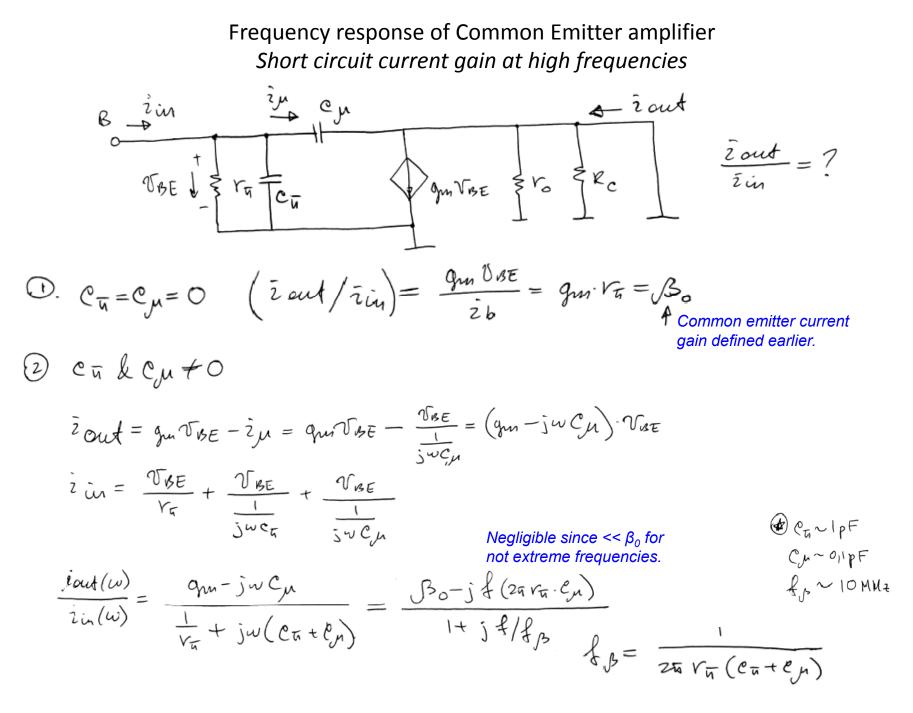




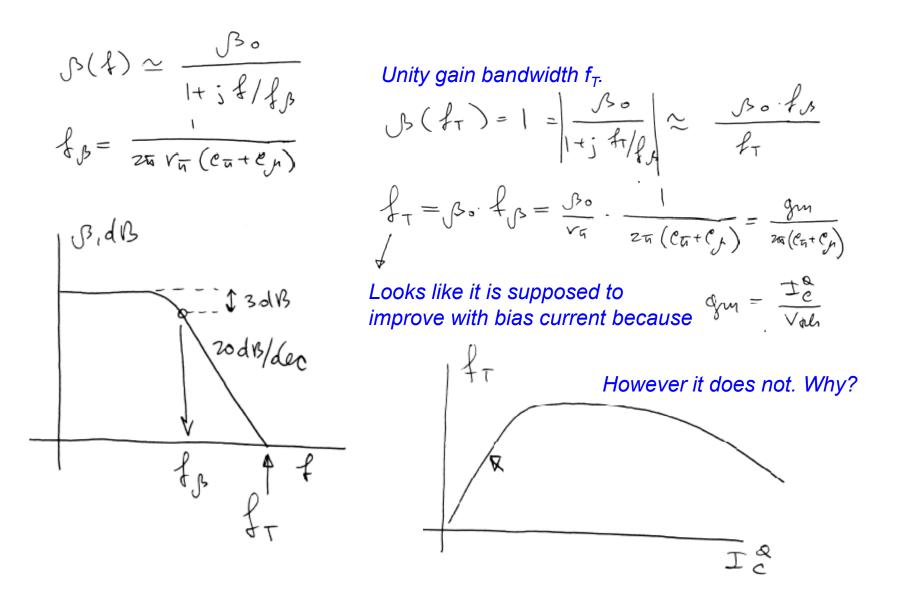
### Frequency response of Common Emitter amplifier Bandwidth



Amplifier bandwidth is determined by BJT high frequency capabilities – determined by internal parasitic capacitances  $C_{\pi}$  and  $C_{\mu}$ .



### Frequency response of Common Emitter amplifier Short circuit current gain at high frequencies

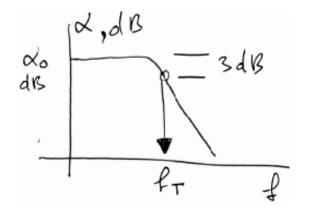


## Frequency response of Common Emitter amplifier Frequency dependence of common base current gain

$$\alpha(f) = \frac{\mathcal{N}(f)}{\mathcal{N}(f) + 1}$$

$$\alpha(f) = \frac{\beta \circ}{1 + \beta \circ + j f/f_{B}} = \frac{\alpha \circ}{1 + j f/(f_{B}(1 + \beta \circ))} \simeq \frac{\alpha \circ}{1 + j f/f_{T}}$$

3dB frequency for  $\alpha$  is equal to  $f_{T}$ .



 $E B C C = \frac{C_{BC0}}{(1 + V_{CB}/V_{bi})^{\frac{1}{2}}}$   $BC-junction \ depletion \ region \ capacitance$ 

$$C_{BE}(V_{BE}) = \frac{C_{BE0}}{(1 - V_{BE}/V_{bi})^{1/2}}$$

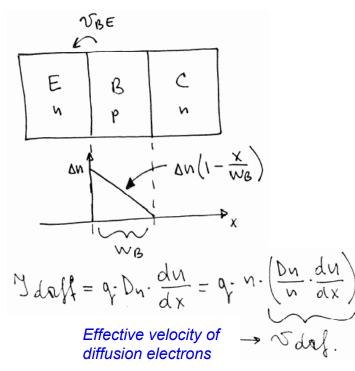
*EB-junction depletion region capacitance* 

Base transport time – time of flight of electrons from emitter to collector.

Hence at  $f_{T}$  electrons from emitter can not reach collector.

> \*There are also several parasitic caps associated with technology limitations

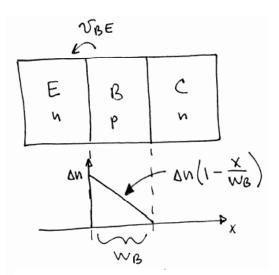
## Frequency response of Common Emitter amplifier Base transport time and associated diffusion capacitance



time of flight of electrons from emitter to collector.

$$\mathcal{T}_{\mathsf{TF}} = \frac{\mathsf{WB}}{\mathsf{Var}} \simeq \frac{\mathsf{WB}^2}{2\mathsf{D}_{\mathsf{N}}}$$

\*Need thin base for high speed operation Frequency response of Common Emitter amplifier Base transport time and associated diffusion capacitance



time of flight of electrons from emitter to collector.

$$\mathcal{T}_{\mathsf{TF}} = \frac{\mathsf{WB}}{\mathsf{Vaill}} \simeq \frac{\mathsf{WB}^2}{2\mathsf{D}_{\mathsf{N}}}$$

\*Need thin base for high speed operation

Electron charge stored in base when current IC is flowing

$$Q_{TF} = I_{c} \cdot T_{TF} \approx q \frac{\Delta N}{2} \cdot W_{B}$$

$$C_{TF} = \frac{d Q_{TF}}{d V_{BE}} \Big|_{I_{c}^{Q}} = T_{TF} \cdot \frac{d I_{c}}{d V_{BE}} \Big|_{I_{c}^{Q}} = T_{TF} \cdot g_{m}$$

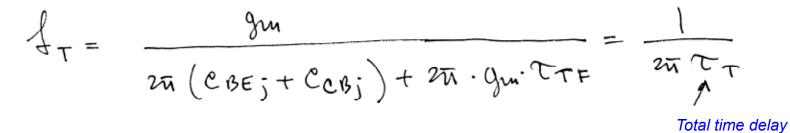
$$C_{TF} = C_{TF} + C_{BE}; ; C_{\mu} = C_{CB};$$

Charge storage capacitance

*Pn-junction depletion region capacitances and other parasitic caps* 

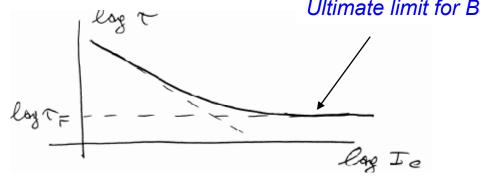
### Frequency response of Common Emitter amplifier Unity gain bandwidth

$$C_{\pi} = C_{TF} + C_{BEj} \& C_{\mu} = C_{CBj}$$
$$= C_{TF} \cdot Q_{M}$$



$$T_T = T_F^+ \frac{C_{BEj} + C_{CBj}}{g_m} \& g_m \sim I_c^2$$

Minimum possible time delay



Ultimate limit for BJT speed